

Silicon NPN Power Transistors

2SD1762

DESCRIPTION

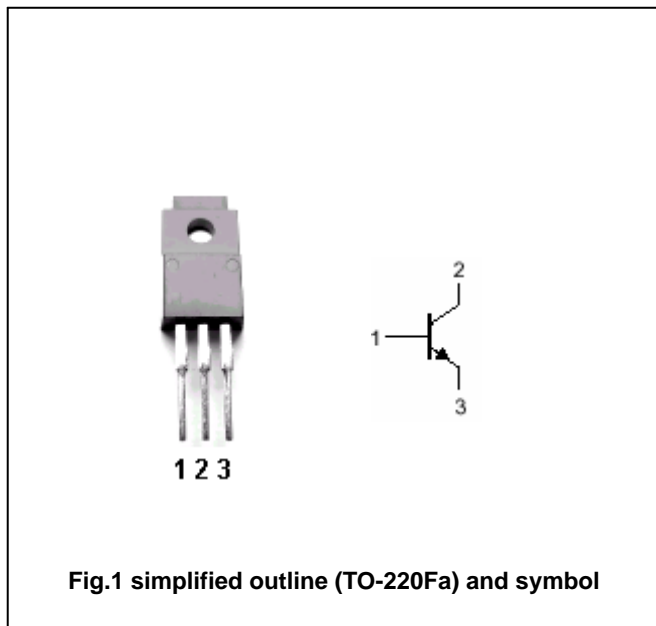
- With TO-220Fa package
- Low collector saturation voltage
- Complement to type 2SB1185

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	60	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	50	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current (DC)		3	A
I <sub>CM</sub>	Collector current-Peak		4.5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	25	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA, I <sub>B</sub> =0	50			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =50 μA, I <sub>E</sub> =0	60			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =50 μA, I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.2A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =40V, I <sub>E</sub> =0			1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =4V; I <sub>C</sub> =0			1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.5A; V <sub>CE</sub> =3V	60		320	
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =-0.5A; V <sub>CE</sub> =5V; f=30MHz		90		MHz
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V, f=1MHz		40		pF

◆ h<sub>FE</sub> Classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

